

1A 40V(0.82mm)

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Chip Information

| | |
|-------------------|-----------------------|
| Chip Size | 0.82 x 0.82mm |
| Pad Size | 0.68 x 0.68mm |
| Chip Quantity | 16276 pcs/wafer |
| Scribe Line Width | 60um |
| Passivation | SIN |
| Wafer Size | 5 inch |
| Top Metallization | Al-Ni-Au (For Solder) |

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

| Parameter | Symbol | Limit | Unit | Note |
|---|---------|-------------|------|-----------------------------|
| Repetitive Peak Reverse Voltage | VRRM | 40 | V | |
| Non-Repetitive Peak Reverse Voltage | VRSM | | V | |
| Maximum DC Blocking Voltage | VR | | V | |
| Average Forward Rectified Current | IF(AV) | 1 | A | |
| Peak Forward Surge Current | IFSM | 40 | A | 8.3ms Single Half Sine-Wave |
| Storage and Operating Temperature Range | Tj,TSTG | -65 to +125 | degC | |

ELECTRICAL CHARACTERISTICS

| Parameter | Symbol | Spec Limit | Probe Spec | Typical | Unit | Test Condition |
|----------------------------|--------|------------|------------|---------|------|--------------------------------------|
| Maximum Forward Voltage | VF1 | 0.500 | | 0.460 | V | IF=1A Ta=25degC |
| | VF2 | | | | V | |
| | VF3 | | | | V | |
| | VF4 | | | | V | |
| | VF5 | | | | V | |
| Maximum DC Reverse Current | IR1 | 0.2 | 0.1 | 0.008 | mA | VR=42V Ta=25degC VR=40V Ta=100deg |
| | IR2 | | | | mA | |
| | IR3 | | | | mA | |
| | IR4 | | | | mA | |
| Reverse Breakdown Voltage | BV | 42 | 44 | 51 | V | IR=0.08mA |
| Junction Capacitance | Cj | | | | pF | |
| Reverse Recovery Time | trr | | | | nS | |

Ordering Information

| Chip Type | Chip Thickness | Back metal |
|-----------|----------------|-----------------------|
| XHT512 | 250 +/- 20um | Ti-Ni-Au (For Solder) |

Note:

Designed For 1N5818,1N5819,B140,SR104